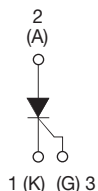
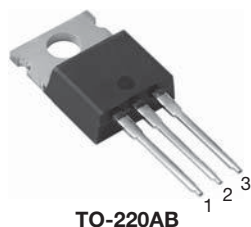


High Voltage Phase Control Thyristor, 12 A



FEATURES

- Designed and qualified according to JEDEC-JESD47
- 125 °C max. operating junction temperature
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

DESCRIPTION

The VS-12TTS08... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

PRODUCT SUMMARY

Package	TO-220AB
Diode variation	Single SCR
$I_{T(AV)}$	8 A
V_{DRM}/V_{RRM}	800 V
V_{TM}	1.2 V
I_{GT}	15 mA
T_J	- 40 °C to 125 °C

OUTPUT CURRENT IN TYPICAL APPLICATIONS

APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	13.5	17	A

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	8	A
$I_{T(RMS)}$		12.5	
V_{DRM}/V_{RRM}		800	V
I_{TSM}		110	A
V_T	8 A, $T_J = 25$ °C	1.2	V
dV/dt		150	V/μs
dI/dt		100	A/μs
T_J	Range	- 40 to 125	°C

VOLTAGE RATINGS

PART NUMBER	V_{RRM} , MAXIMUM PEAK VOLTAGE V	V_{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM}/I_{DRM} AT 125 °C mA
VS-12TTS08PbF, VS-12TTS08-M3	800	800	1.0

**ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average on-state current	$I_{T(AV)}$	$T_C = 108\text{ }^{\circ}\text{C}$, 180° conduction, half sine wave	8	A
Maximum RMS on-state current	$I_{T(RMS)}$		12.5	
Maximum peak, one-cycle, non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied, $T_J = 125\text{ }^{\circ}\text{C}$	95	
		10 ms sine pulse, no voltage reapplied, $T_J = 125\text{ }^{\circ}\text{C}$	110	
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied, $T_J = 125\text{ }^{\circ}\text{C}$	45	A^2s
		10 ms sine pulse, no voltage reapplied, $T_J = 125\text{ }^{\circ}\text{C}$	64	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1\text{ ms to }10\text{ ms}$, no voltage reapplied, $T_J = 125\text{ }^{\circ}\text{C}$	640	$\text{A}^2\sqrt{\text{s}}$
Maximum on-state voltage drop	V_{TM}	8 A, $T_J = 25\text{ }^{\circ}\text{C}$	1.2	V
On-state slope resistance	r_t	$T_J = 125\text{ }^{\circ}\text{C}$	16.2	$\text{m}\Omega$
Threshold voltage	$V_{T(TO)}$		0.87	V
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	$T_J = 25\text{ }^{\circ}\text{C}$	0.05	mA
		$T_J = 125\text{ }^{\circ}\text{C}$	1.0	
Typical holding current	I_H	Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$, $T_J = 25\text{ }^{\circ}\text{C}$	30	
			50	
Maximum latching current	I_L	Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$	50	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J\text{ max.}$, linear to $80\text{ }^{\circ}\text{C}$, $V_{DRM} = R_g - k = \text{Open}$	150	$\text{V}/\mu\text{s}$
Maximum rate of rise of turned-on current	dI/dt		100	$\text{A}/\mu\text{s}$

TRIGGERING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}		8.0	W
Maximum average gate power	$P_{G(AV)}$		2.0	
Maximum peak positive gate current	$+I_{GM}$		1.5	A
Maximum peak negative gate voltage	$-V_{GM}$		10	V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, $T_J = -65\text{ }^{\circ}\text{C}$	20	mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$	15	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^{\circ}\text{C}$	10	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = -65\text{ }^{\circ}\text{C}$	1.2	V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$	1	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^{\circ}\text{C}$	0.7	
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125\text{ }^{\circ}\text{C}$, $V_{DRM} = \text{Rated value}$	0.2	mA
Maximum DC gate current not to trigger	I_{GD}		0.1	

SWITCHING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t_{gt}	$T_J = 25\text{ }^{\circ}\text{C}$	0.8	μs
Typical reverse recovery time	t_{rr}	$T_J = 125\text{ }^{\circ}\text{C}$	3	
Typical turn-off time	t_q		100	



THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		- 40 to 125	°C
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.5	°C/W
Maximum thermal resistance, junction to ambient	R _{thJA}		62	
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight			2	g
			0.07	oz.
Mounting torque	minimum		6 (5)	kgf · cm (lbf · in)
	maximum		12 (10)	
Marking device		Case style TO-220AB	12TTS08	

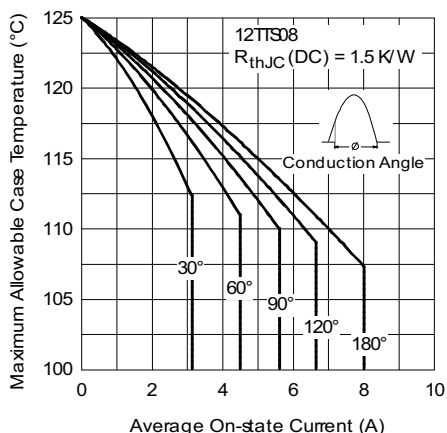


Fig. 1 - Current Ratings Characteristics

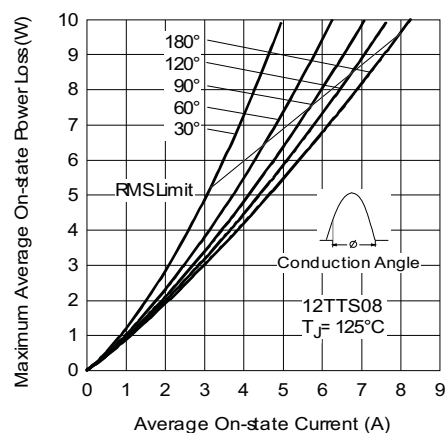


Fig. 3 - On-State Power Loss Characteristics

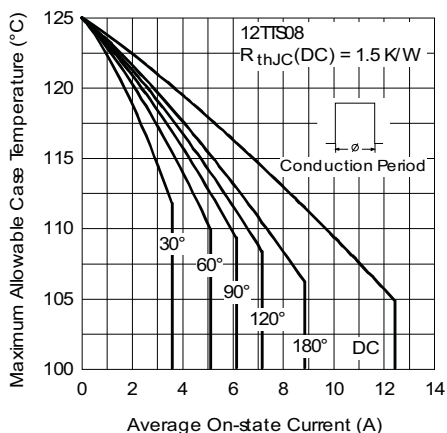


Fig. 2 - Current Ratings Characteristics

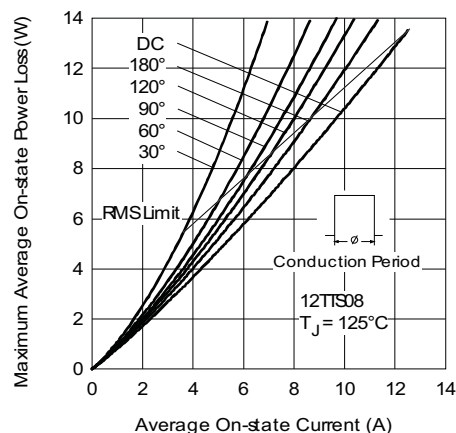


Fig. 4 - On-State Power Loss Characteristics

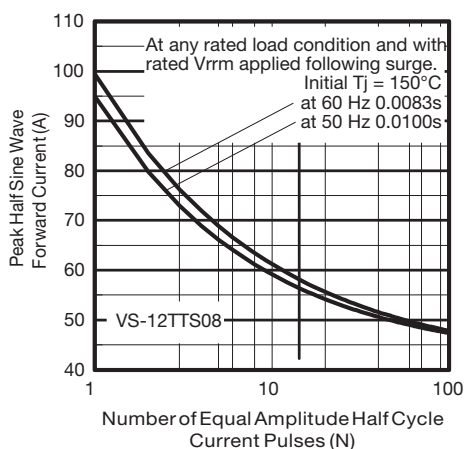


Fig. 5 - Maximum Non-Repetitive Surge Current

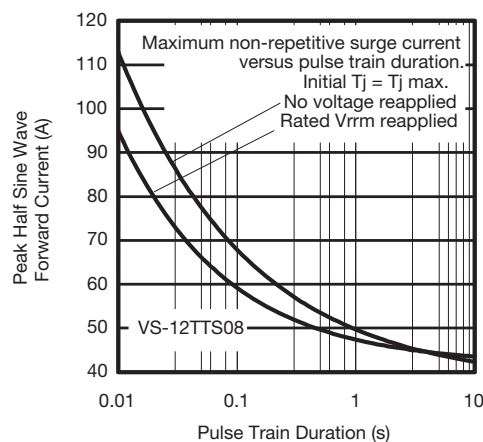


Fig. 6 - Maximum Non-Repetitive Surge Current

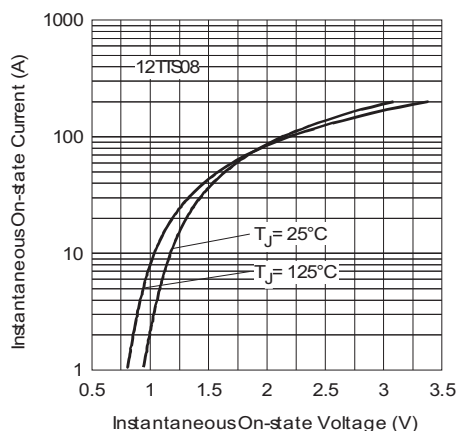
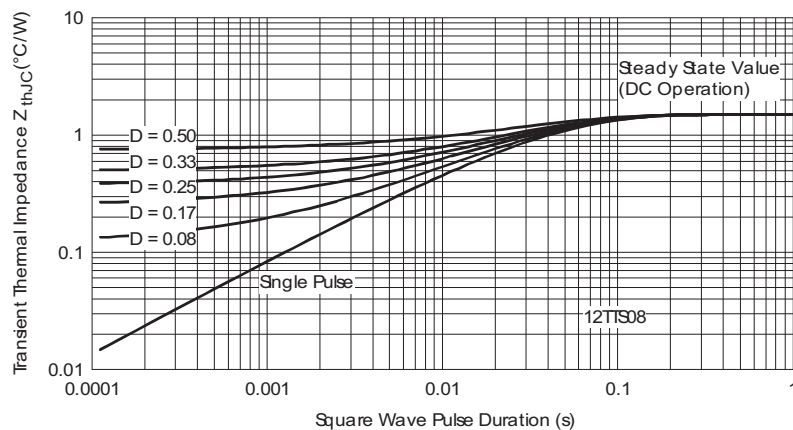


Fig. 7 - On-State Voltage Drop Characteristics


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

**ORDERING INFORMATION TABLE**

Device code	VS-	12	T	T	S	08	PbF
	1	2	3	4	5	6	7

- 1** - Vishay Semiconductors product
- 2** - Current ratings (12 = 12.5 A)
- 3** - Circuit configuration:
T = Single thyristor
- 4** - Package:
T = TO-220
- 5** - Type of silicon
S = Standard recovery rectifier
- 6** - Voltage rating (08 = 800 V)
- 7** - Environmental digit:
PbF = Lead (Pb)-free and RoHS compliant
-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-12TTS08PbF	50	1000	Antistatic plastic tubes
VS-12TTS08-M3	50	1000	Antistatic plastic tubes

LINKS TO RELATED DOCUMENTS		
Dimensions		www.vishay.com/doc?95222
Part marking information	TO-220AB PbF	www.vishay.com/doc?95225
	TO-220AB -M3	www.vishay.com/doc?95028



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<http://moschip.ru/get-element>

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